

**COMPOUND SEMICONDUCTOR DEVICE**

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Abstract

PROBLEM TO BE SOLVED: To provide a nitride compound semiconductor device having high reliability.
SOLUTION: Conductive aluminum oxide is used as a growth substrate 101 of a nitride compound semiconductor device 100. To provide the substrate 101 with conductivity, impurities are introduced into the substrate 101, for example. Due to the conductivity of the substrate 101, there is no need to conduct etching or the like to establish electric contact with internal layers which do not appear on the surface of a layered structure. As a result, a device can be formed without damage caused by processing an epitaxial layer.

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